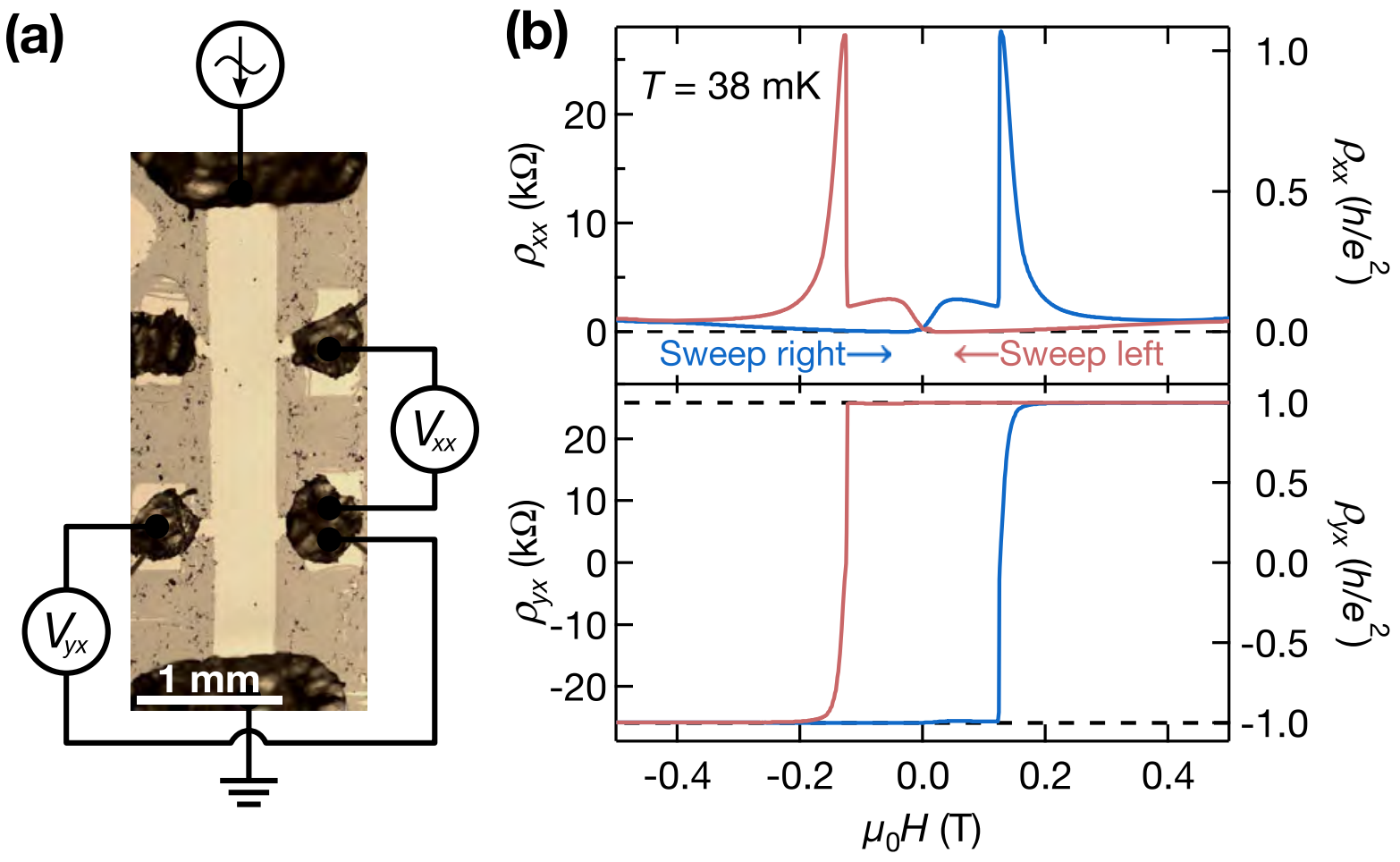

FIG. 1 (color online). Device demonstrating quantum anomalous Hall effect. (a) Photograph of 10-nm-thick film of $(Cr_{0.12}Bi_{0.26}Sb_{0.62})_2Te_3$ on a GaAs substrate, scratched by hand into a Hall bar shape, with indium metal Ohmic contacts. Schematic measurement setup included. (b) Longitudinal resistivity ρ_{xx} and transverse resistivity ρ_{yx} of the device at base temperature as a function of the applied magnetic field $\mu_0 H$ in each sweep direction, forming a ferromagnetic hysteresis loop. As the field approaches zero from either starting point, ρ_{yx} reaches its quantized value h/e^2 and ρ_{xx} approaches zero.